

AMENDMENT TRANSMITTAL LETTER

Docket No.
M4065.0210/P210Application No.
09/588,008Filing Date
June 6, 2000Examiner
H. TrinhArt Unit
2814

MAR 20 2002

Applicant(s): Dan Gealy, et al.

Invention: IMPROVED MEMORY CELL CAPACITOR STRUCTURE AND METHOD OF FORMATION

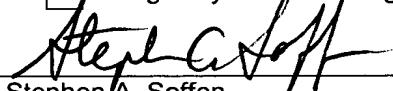
TO THE COMMISSIONER FOR PATENTS

Transmitted herewith is an amendment in the above-identified application.

The fee has been calculated and is transmitted as shown below.

CLAIMS AS AMENDED

	Claims Remaining After Amendment	Highest Number Previously Paid	Number Extra Claims Present	Rate	
Total Claims	31	- 96 =	0	x	0.00
Independent Claims	3	- 3 =	0	x	
Multiple Dependent Claims (check if applicable) <input type="checkbox"/>					
Other fee (please specify):					
TOTAL ADDITIONAL FEE FOR THIS AMENDMENT:					

 Large Entity Small Entity No additional fee is required for this amendment. Please charge Deposit Account No. _____ in the amount of \$ _____.
A duplicate copy of this sheet is enclosed. A check in the amount of \$ _____ to cover the filing fee is enclosed. The Commissioner is hereby authorized to charge and credit Deposit Account No. 04-1073
as described below. A duplicate copy of this sheet is enclosed. Credit any overpayment. Charge any additional filing or application processing fees required under 37 CFR 1.16 and 1.17.
Stephen A. Soffen

Attorney Reg. No.: 31,063

Dated: March 20, 2002

DICKSTEIN SHAPIRO MORIN & OSHINSKY LLP
2101 L Street NW
Washington, DC 20037-1526
(202) 785-9700



Docket No.: M4065.0210/P210
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Dan Gealy, et al.

Application No.: 09/588,008

Group Art Unit: 2814

Filed: June 6, 2000

Examiner: H. Trinh

For: IMPROVED MEMORY CELL CAPACITOR
STRUCTURE AND METHOD OF
FORMATION

RECEIVED
MAR 21 2002
TECHNOLOGY CENTER 2800
774/alpha
3/28/02
DBo

REQUEST FOR RECONSIDERATION

Box Non-Fee Amendment
Commissioner for Patents
Washington, DC 20231

Dear Sir:

In response to the Office Action dated January 3, 2002 (Paper No. 6), please reconsider the above-identified U.S. Patent application in view of the following remarks:

In the Claims:

Please add the following new claims:

97. (new) A capacitor for a semiconductor device, said capacitor comprising:

a tungsten nitride bottom layer;

a tantalum pentoxide layer over said tungsten nitride bottom layer; and

an annealed platinum layer over said dielectric layer.